

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

1-18. (Canceled)

19. (Currently Amended) A method for manufacturing a light-emitting device, comprising:

forming a thin film transistor over a substrate;

forming a first insulating film over the thin film transistor;

performing a first plasma treatment on the first insulating film after forming the first insulating film;

forming a first electrode over the first insulating film, wherein the first electrode is electrically connected to the thin film transistor;

forming a second insulating film over the first insulating film and an edge portion of the first electrode;

performing a second plasma treatment at least on the second insulating film after forming the second insulating film;

forming a polymer film on the first electrode and the second insulating film;

forming a low molecular weight film on the polymer film; and

forming a second electrode on the low molecular weight film.

20. (Previously presented) A method according to claim 1, wherein the polymer film is a luminescent layer and the low molecular weight film is an electron transport layer or an electron injection layer.

21. (Previously presented) A method according to claim 1, wherein the light emitting device is incorporated into an electronic device selected from the group consisting of a video

camera, a digital camera, a goggle type display, a navigation system, a personal computer, a portable information terminal.

22. (Currently Amended) A method for manufacturing a light-emitting device, comprising:

forming a thin film transistor over a substrate;

forming a first insulating film over the thin film transistor;

performing a first plasma treatment on the first insulating film after forming the first insulating film;

forming a first electrode over the first insulating film, wherein the first electrode is electrically connected to the thin film transistor;

forming a second insulating film over the first insulating film and an edge portion of the first electrode;

performing a second plasma treatment at least on the second insulating film after forming the second insulating film;

forming a polymer film on the first electrode and the second insulating film;

forming a low molecular weight film on the polymer film; and

forming a second electrode on the low molecular weight film,

wherein upper surfaces of the first and second insulating films are hardened by performing the first and second plasma treatments.

23. (Previously presented) A method according to claim 22, wherein the polymer film is a luminescent layer and the low molecular weight film is an electron transport layer or an electron injection layer.

24. (Previously presented) A method according to claim 22, wherein the light emitting device is incorporated into an electronic device selected from the group consisting of a video

camera, a digital camera, a goggle type display, a navigation system, a personal computer, a portable information terminal.

25. (Currently Amended) A method for manufacturing a light-emitting device, comprising:

forming a thin film transistor over a substrate;

forming a first insulating film over the thin film transistor;

performing a plasma treatment on the first insulating film after forming the first insulating film;

forming a first electrode over the first insulating film, wherein the first electrode is electrically connected to the thin film transistor;

forming a second insulating film over the first insulating film and an edge portion of the first electrode;

forming a third-insulating diamond-like carbon film over the second insulating film;

forming a polymer film on the first electrode and the second-insulating diamond-like carbon film;

forming a low molecular weight film on the polymer film; and

forming a second electrode on the low molecular weight film[.];

~~wherein the third-insulating film is a diamond-like carbon or a silicon nitride film.~~

26. (Previously presented) A method according to claim 25, wherein the polymer film is a luminescent layer and the low molecular weight film is an electron transport layer or an electron injection layer.

27. (Previously presented) A method according to claim 25, wherein the light emitting device is incorporated into an electronic device selected from the group consisting of a video camera, a digital camera, a goggle type display, a navigation system, a personal computer, a portable information terminal.

28. (Currently Amended) A method for manufacturing a light-emitting device, comprising:

forming a thin film transistor over a substrate;

forming a first insulating film over the thin film transistor;

performing a plasma treatment on the first insulating film after forming the first insulating film;

forming a first electrode over the first insulating film, wherein the first electrode is electrically connected to the thin film transistor;

forming a second insulating film over the first insulating film and an edge portion of the first electrode;

forming a third-insulating diamond-like carbon film on the second insulating film;

forming a polymer film on the first electrode and the second-insulating diamond-like carbon film;

forming a low molecular weight film on the polymer film; and

forming a second electrode on the low molecular weight film,

~~wherein the third-insulating film is a diamond-like carbon or a silicon nitride film, and~~

wherein an upper surface of the first insulating film is hardened by performing the plasma treatment.

29. (Previously presented) A method according to claim 28, wherein the polymer film is a luminescent layer and the low molecular weight film is an electron transport layer or an electron injection layer.

30. (Previously presented) A method according to claim 28, wherein the light emitting device is incorporated into an electronic device selected from the group consisting of a video camera, a digital camera, a goggle type display, a navigation system, a personal computer, a portable information terminal.

31. (Currently Amended) A method for manufacturing a light-emitting device, comprising:

- forming a thin film transistor over a substrate;
- forming a first ~~insulating~~ film over the thin film transistor;
- forming a second insulating film on the first ~~insulating~~ film;
- forming a first electrode over the second ~~insulating~~ film, wherein the first electrode is electrically connected to the thin film transistor;
- forming a third ~~insulating~~ film over the second ~~insulating~~ film and an edge portion of the first electrode;
- forming a fourth ~~insulating~~ film on the third ~~insulating~~ film;
- forming a polymer film on the first electrode and the ~~second-insulating~~ fourth film;
- forming a low molecular weight film on the polymer film; and
- forming a second electrode on the low molecular weight film,

wherein the second and fourth films are insulating, ~~film is a diamond-like carbon or a silicon nitride film~~ films.

32. (Previously presented) A method according to claim 31, wherein the polymer film is a luminescent layer and the low molecular weight film is an electron transport layer or an electron injection layer.

33. (Previously presented) A method according to claim 31, wherein the light emitting device is incorporated into an electronic device selected from the group consisting of a video camera, a digital camera, a goggle type display, a navigation system, a personal computer, a portable information terminal.